

Ordering number : ENN7039

P-Channel Silicon MOSFET



# MCH6607

## Ultrahigh-Speed Switching Applications

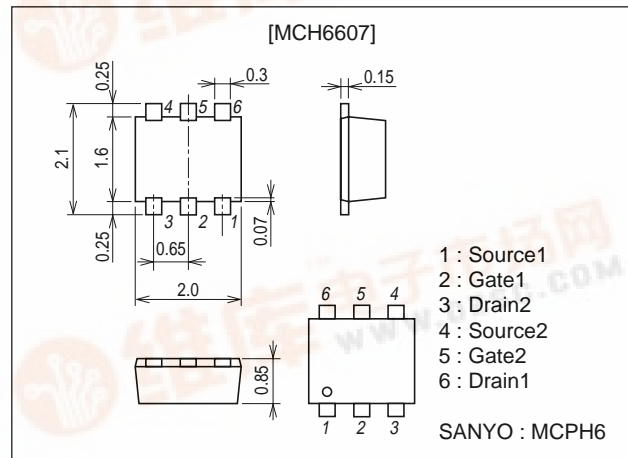
### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.

### Package Dimensions

unit : mm

2173A



### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-0.4	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-1.6	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm²×0.8mm)1unit	0.8	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-100mA	210	300		mS
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-100mA, V <sub>GS</sub> =-4V		2.4	3.1	Ω
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-50mA, V <sub>GS</sub> =-2.5V		3.5	4.9	Ω
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-10mA, V <sub>GS</sub> =-1.5V		10	20	Ω

Marking : FG

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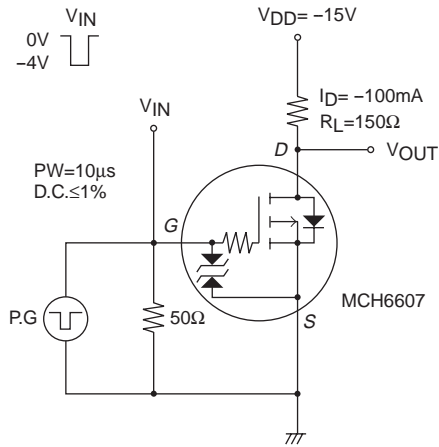


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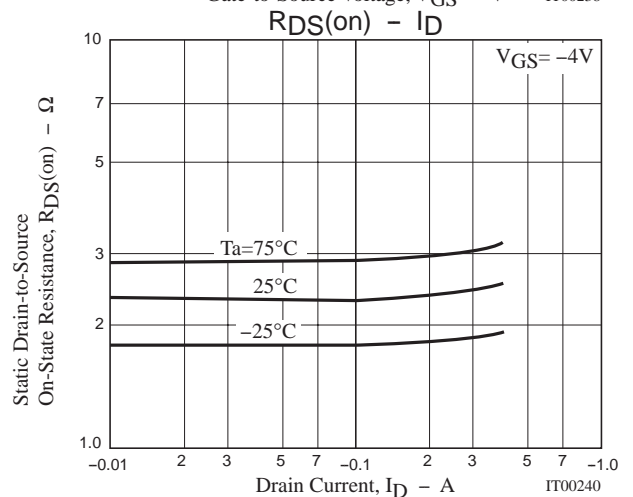
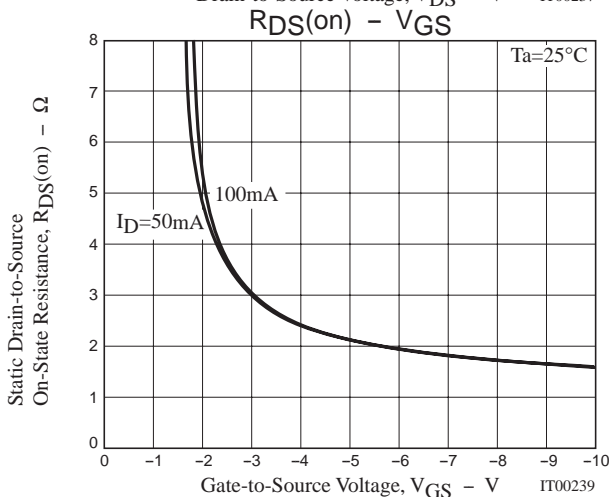
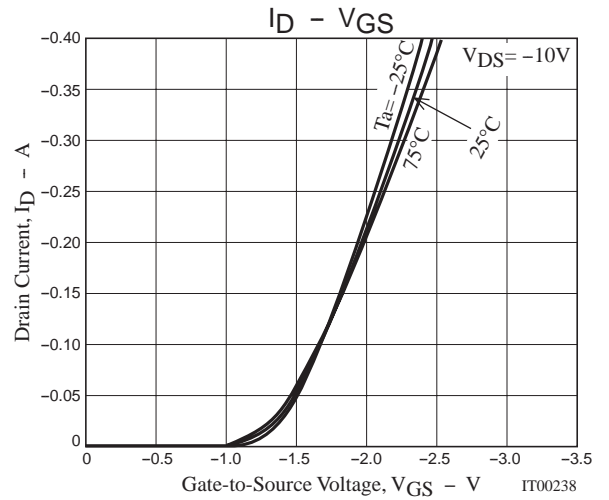
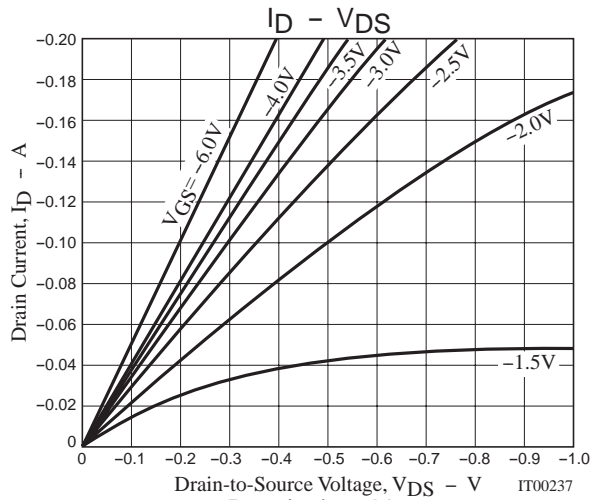
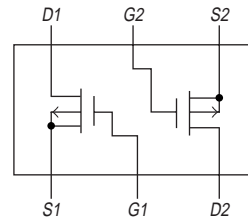
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, f=1MHz$		28		pF
Output Capacitance	$C_{oss}$	$V_{DS}=-10V, f=1MHz$		15		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=-10V, f=1MHz$		5.2		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		24		ns
Rise Time	$t_r$	See specified Test Circuit.		75		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		200		ns
Fall Time	$t_f$	See specified Test Circuit.		150		ns
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		2		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		0.25		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		0.35		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-200mA, V_{GS}=0$		-0.82	-1.2	V

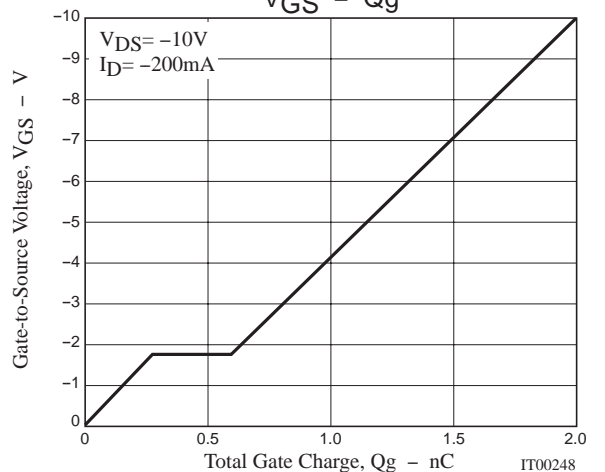
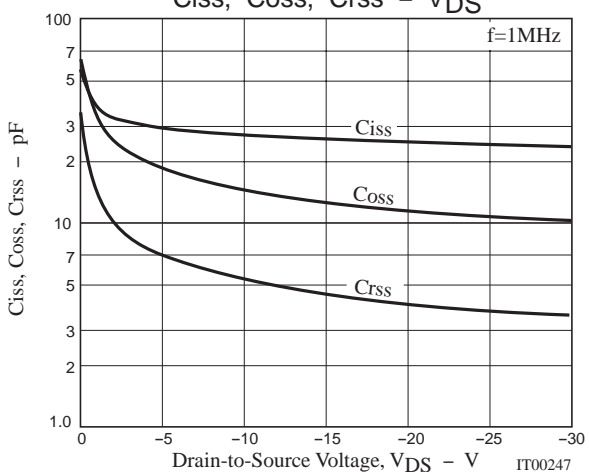
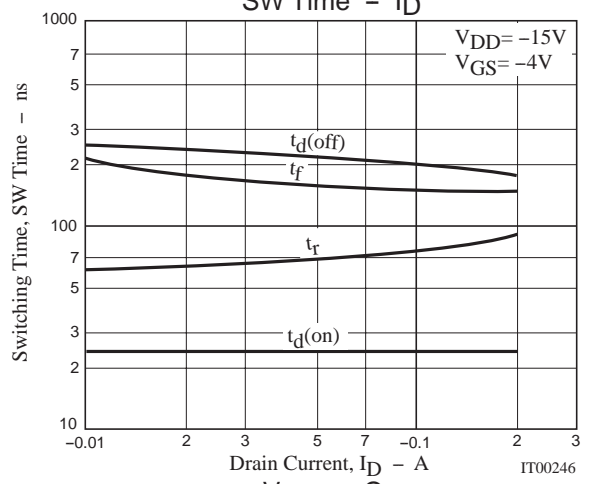
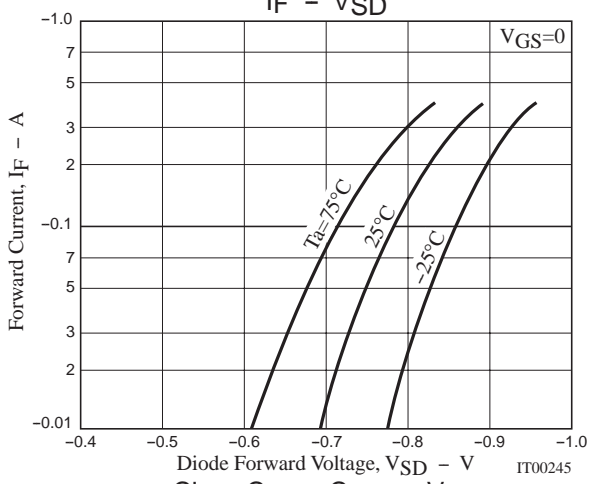
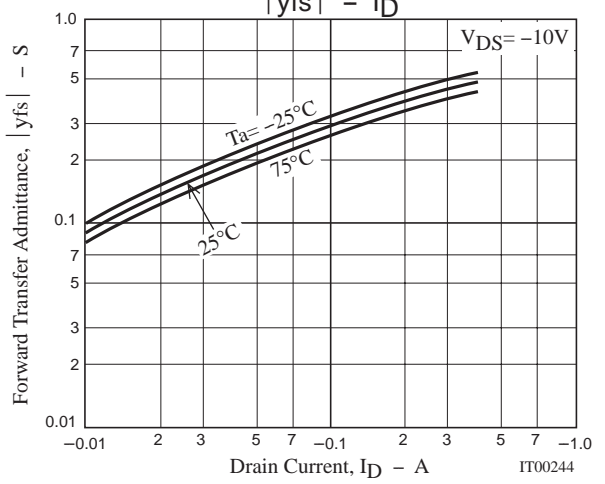
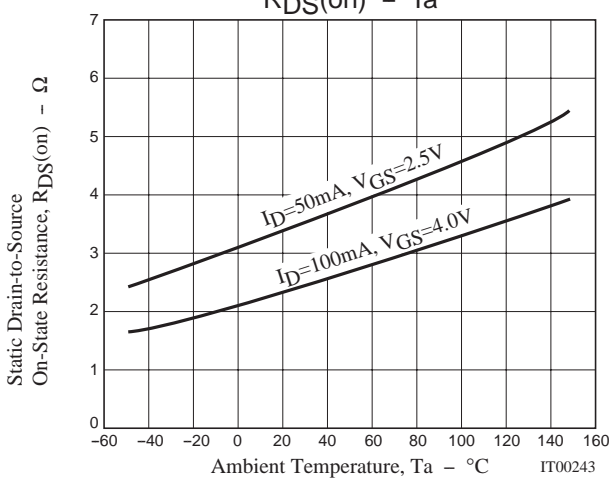
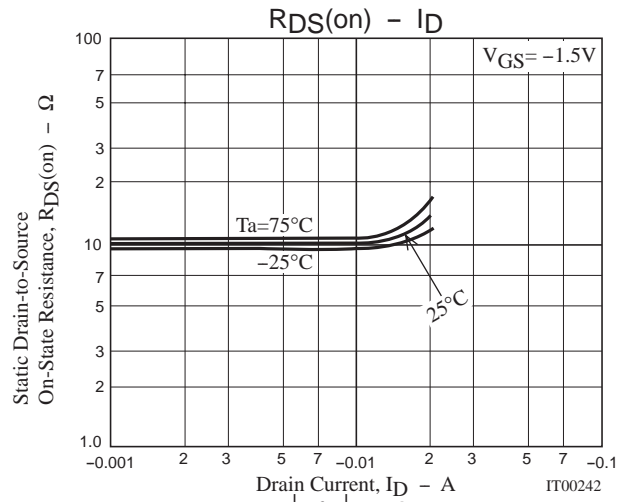
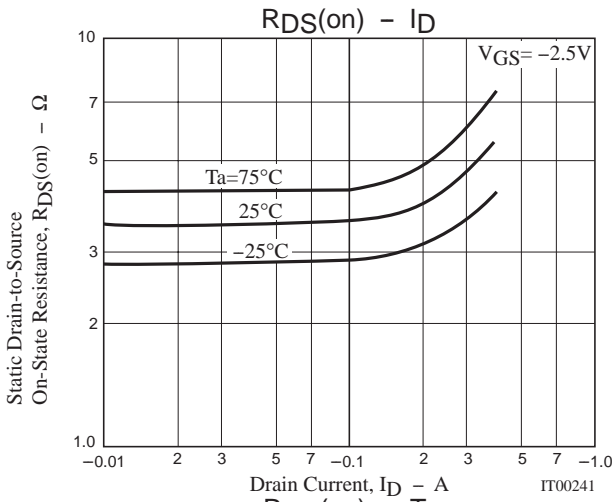
## Switching Time Test Circuit



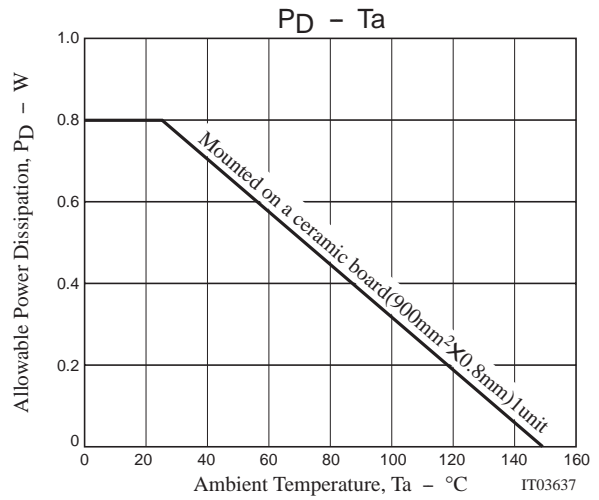
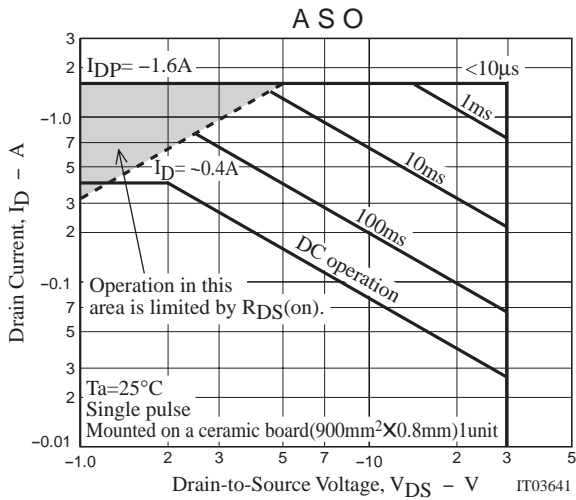
## Electrical Connection



# MCH6607



## MCH6607



Note on usage : Since the MCH6607 is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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